N-Channel Silicon MOSFET



2SK1443LS

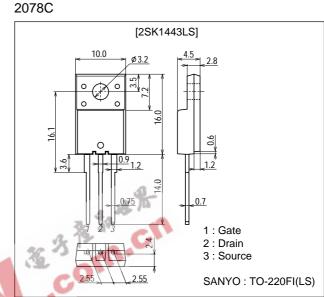
Ultrahigh-Speed Switching Applications

Features

- · Low ON-resistance.
- Ultrahigh-speed switching.
- · Micaless package facilitating mounting.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter		Symbol		Conditions	Ratings	Unit
Drain-to-Source Voltage		VDSS			450	V
Gate-to-Source Voltage		VGSS			±30	V
Drain Current (DC)		ID			1	А
Drain Current (Pulse)		IDP	PW≤10µ	ls, duty cycle≤1%	4	А
Allowable Power Dissipation		PD			2.0	W
			Tc=25°C	:	20	W
Channel Temperature		Tch			150	°C
Storage Temperature		Tstg			-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	450			V
Zero-Gate Voltage Drain Current	IDSS	VDS=450V, VGS=0			1.0	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0			±100	nA

(Note) Be careful in handling the 2SK1443LS because it has no protection diode between gate and source.

Continued on next page.

Marking: K1443

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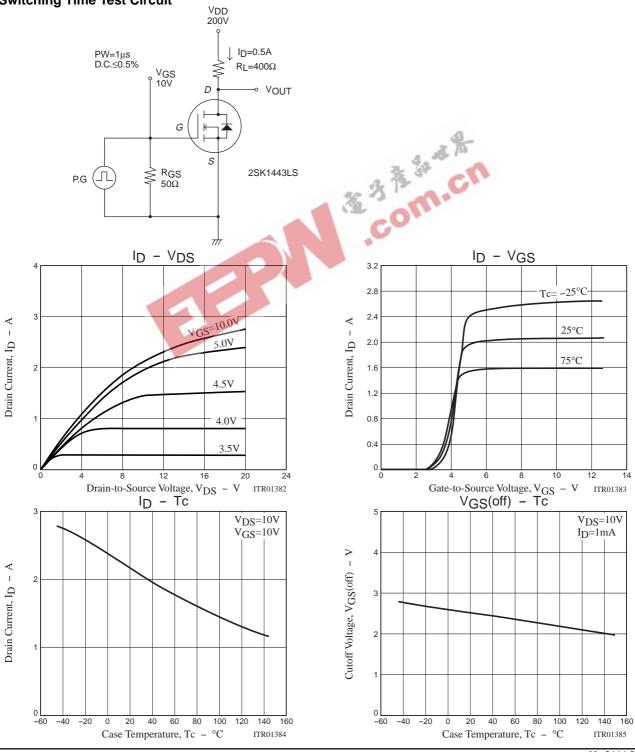
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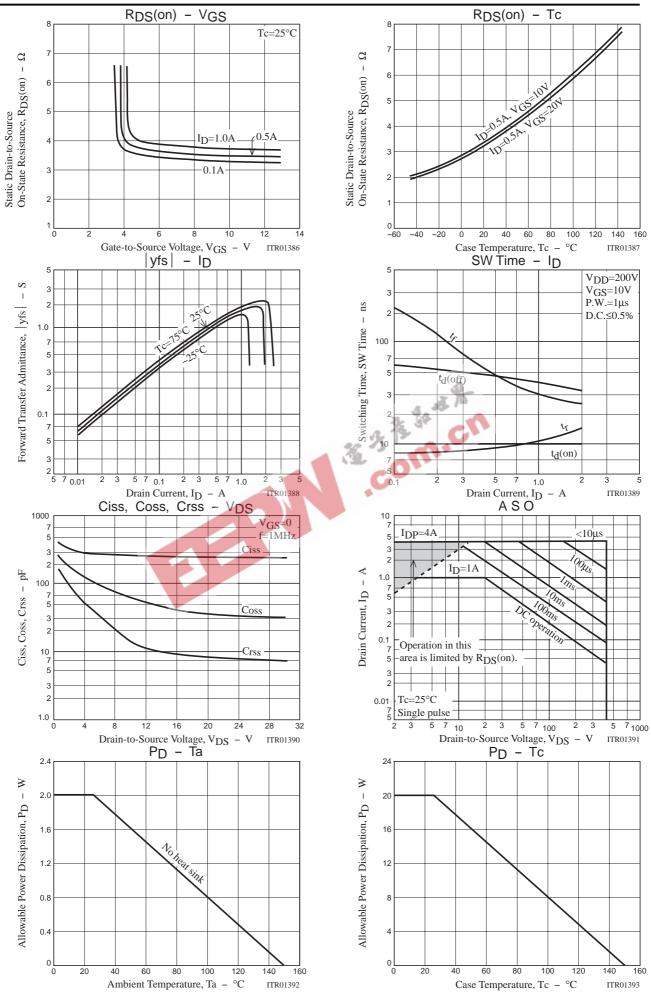
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Parameter	Symbol	Conditions	Ratings			Unit
Falameter	Symbol	Conditions	min	typ	max	Unit
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.0		3.0	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =0.5A	0.6	1.2		S
Static Drain-to-Source On-State Resistance	RDS(on)	ID=0.5A, VGS=10V		3.5	4.5	Ω
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		250		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		40		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		8		pF
Turn-ON Delay Time	t _d (on)	ID=0.5A, V_{GS} =10V, V_{DD} =200V, R_{GS} =50 Ω		10		ns
Rise Time	tr	ID=0.5A, VGS=10V, VDD=200V, RGS=50Ω		9		ns
Turn-OFF Delay Time	t _d (off)	ID=0.5A, VGS=10V, VDD=200V, RGS=50Ω		45		ns
Fall Time	tf	ID=0.5A, VGS=10V, VDD=200V, RGS=50Ω		45		ns
Diode Forward Voltage	V _{SD}	IS=1A, VGS=0			1.8	V

Switching Time Test Circuit





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